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[SIS415DNT-T1-GE3](#)

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SiS415DNT

Vishay Siliconix

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A)	Q _g (Typ.)
- 20	0.0040 at V _{GS} = - 10 V	- 35 ^a	55.5 nC
	0.0055 at V _{GS} = - 4.5 V	- 35 ^a	
	0.0095 at V _{GS} = - 2.5 V	- 35 ^a	

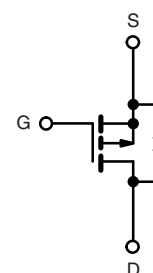
FEATURES

- TrenchFET[®] Gen III P-Channel Power MOSFET
- Thin 0.8 mm max. height
- 100 % R_g and UIS Tested
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912

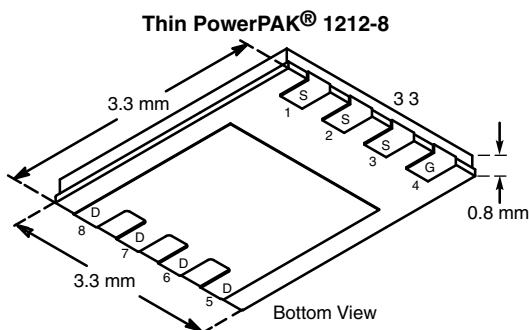

**RoHS
COMPLIANT
HALOGEN
FREE**

APPLICATIONS

- Smart Phones, Tablet PCs, and Mobile Computing
- Battery Switch
- Load Switch
- Power Management



P-Channel MOSFET


Ordering Information:
 SiS415DNT-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	- 20	V
Gate-Source Voltage		V _{GS}	± 12	
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	I _D	- 35 ^a	A
	T _C = 70 °C		- 35 ^a	
	T _A = 25 °C		- 22.6 ^{b, c}	
	T _A = 70 °C		- 18.2 ^{b, c}	
Pulsed Drain Current (t = 300 μs)		I _{DM}	- 80	
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 35 ^a	
	T _A = 25 °C		- 3.3 ^{b, c}	
Avalanche Current		I _{AS}	- 20	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	20	mJ
Maximum Power Dissipation	T _C = 25 °C	P _D	52	W
	T _C = 70 °C		33	
	T _A = 25 °C		3.7 ^{b, c}	
	T _A = 70 °C		2.4 ^{b, c}	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}			260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	t ≤ 10 s	R _{thJA}	26	33	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	1.9	2.4	

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 81 °C/W.

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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 20			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 14		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J		3.1				
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.4		- 1.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 12 V			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V			- 1	μA	
		V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ - 5 V, V _{GS} = - 10 V	- 30			A	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 20 A		0.0033	0.0040	Ω	
		V _{GS} = - 4.5 V, I _D = - 15 A		0.0044	0.0055		
		V _{GS} = - 2.5 V, I _D = - 10 A		0.0076	0.0095		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 20 A		70		S	
Dynamic^b							
Input Capacitance	C _{iss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		5460		pF	
Output Capacitance	C _{oss}		645				
Reverse Transfer Capacitance	C _{rss}		642				
Total Gate Charge	Q _g	V _{DS} = - 10 V, V _{GS} = - 10 V, I _D = - 10 A		117	180	nC	
			V _{DS} = - 10 V, V _{GS} = - 4.5 V, I _D = - 10 A		55.5		85
							7.9
Gate-Source Charge	Q _{gs}			12.7			
Gate-Drain Charge	Q _{gd}						
Gate Resistance	R _g	f = 1 MHz	0.4	2.2	4	Ω	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 1 Ω I _D ≅ - 10 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		37	70	ns	
Rise Time	t _r			38	70		
Turn-Off Delay Time	t _{d(off)}			82	150		
Fall Time	t _f			25	50		
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 10 V, R _L = 1 Ω I _D ≅ - 10 A, V _{GEN} = - 10 V, R _g = 1 Ω		14	25	ns	
Rise Time	t _r			13	25		
Turn-Off Delay Time	t _{d(off)}			83	150		
Fall Time	t _f			14	25		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 35	A	
Pulse Diode Forward Current	I _{SM}				- 80		
Body Diode Voltage	V _{SD}	I _S = - 4 A, V _{GS} = 0 V		- 0.72	- 1.1	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 10 A, di/dt = 100 A/μs, T _J = 25 °C		25	50	ns	
Body Diode Reverse Recovery Charge	Q _{rr}				12	24	nC
Reverse Recovery Fall Time	t _a				11		ns
Reverse Recovery Rise Time	t _b				14		

Notes:

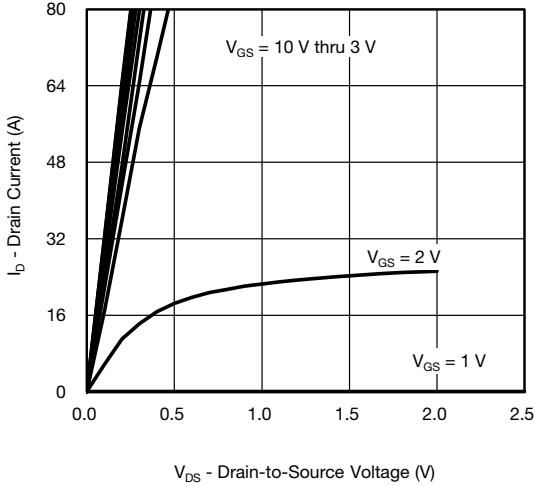
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

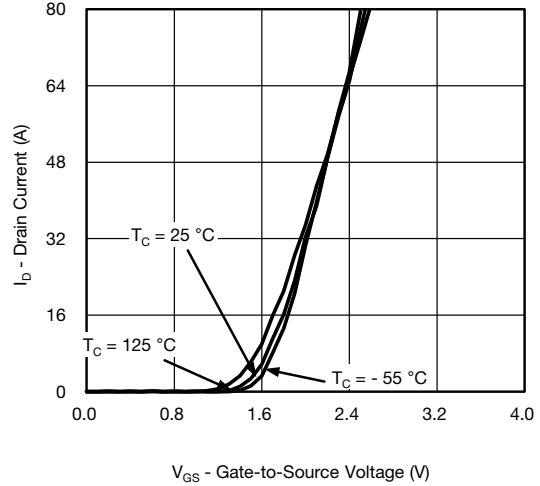


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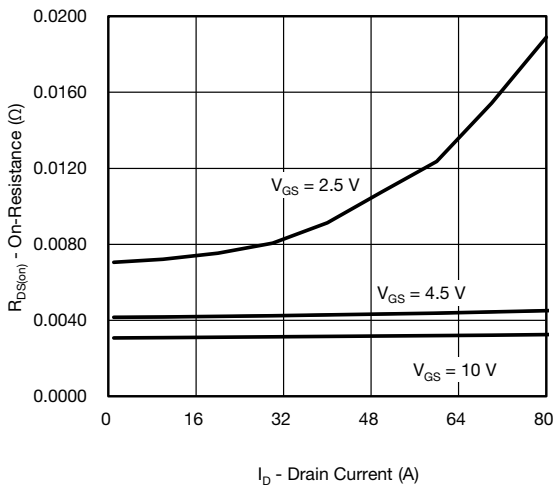
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



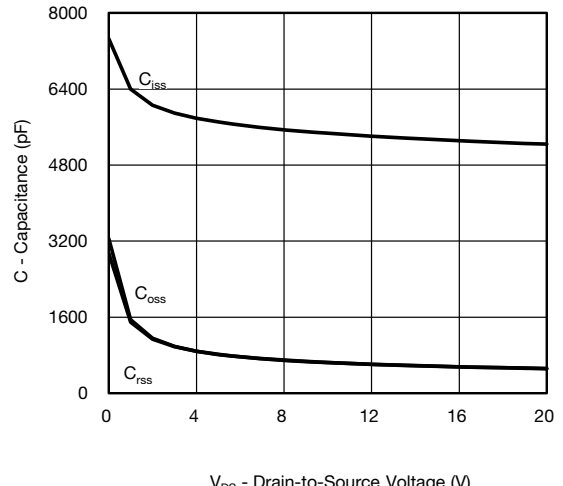
V_{DS} - Drain-to-Source Voltage (V)
Output Characteristics



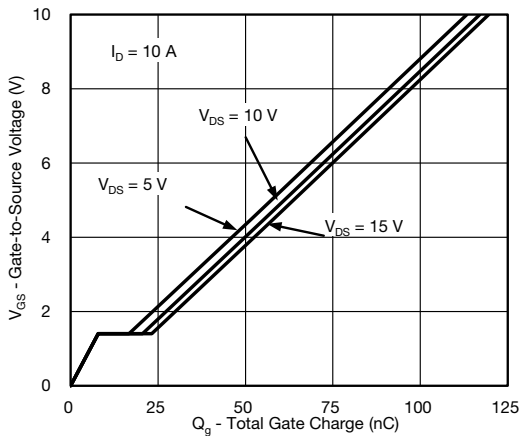
V_{GS} - Gate-to-Source Voltage (V)
Transfer Characteristics



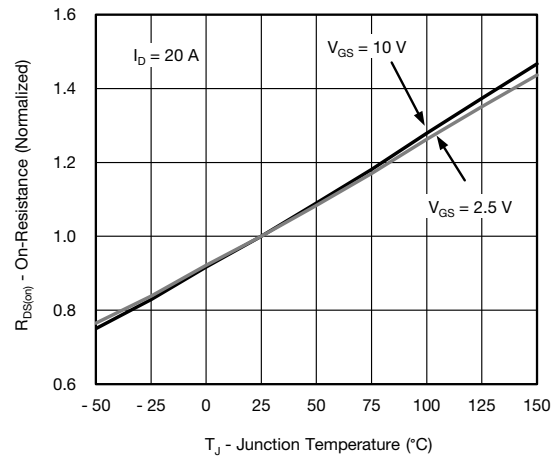
I_D - Drain Current (A)
On-Resistance vs. Drain Current and Gate Voltage



V_{DS} - Drain-to-Source Voltage (V)
Capacitance



Gate Charge



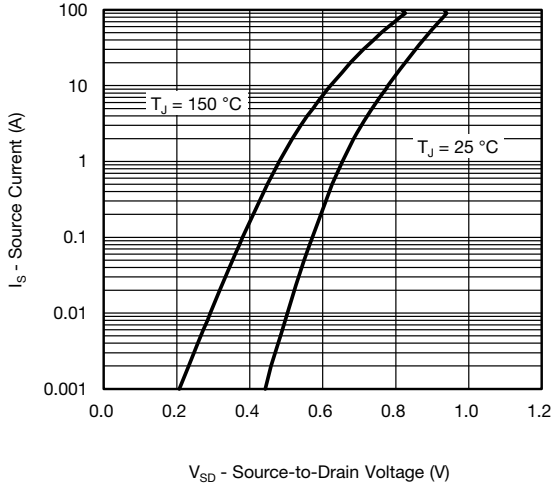
On-Resistance vs. Junction Temperature

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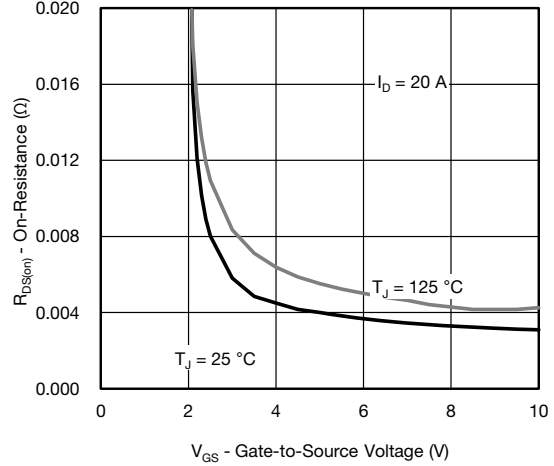
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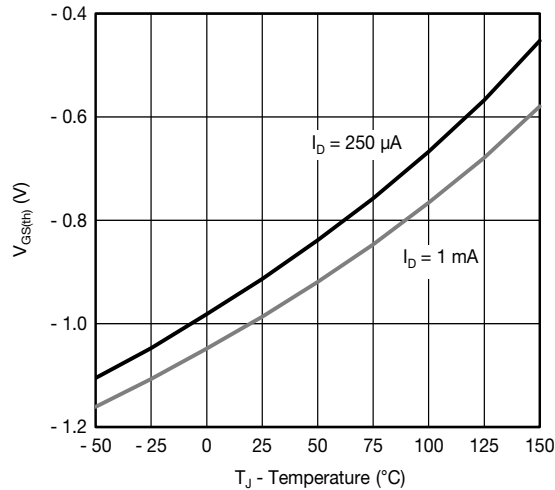
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



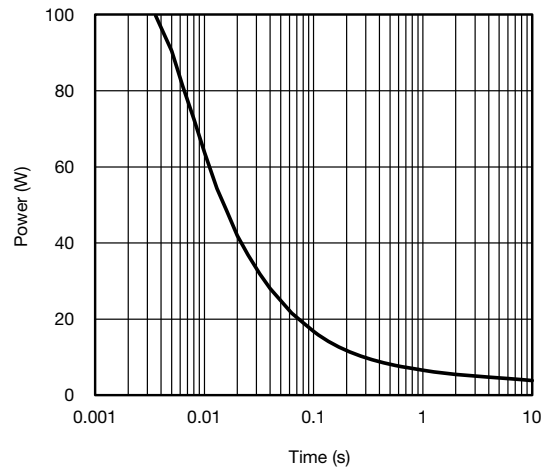
Source-Drain Diode Forward Voltage



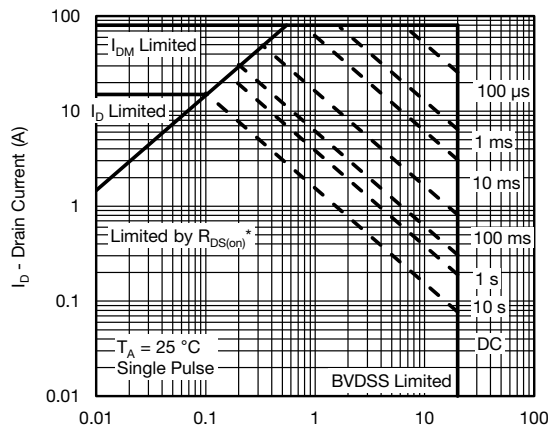
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient

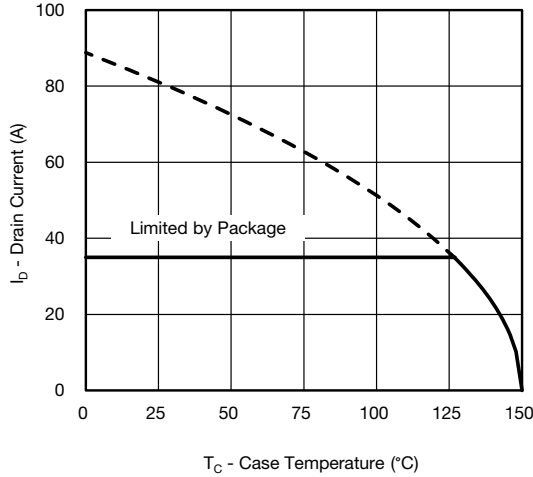


* $V_{GS} >$ minimum V_{GS} at which $R_{D(on)}$ is specified

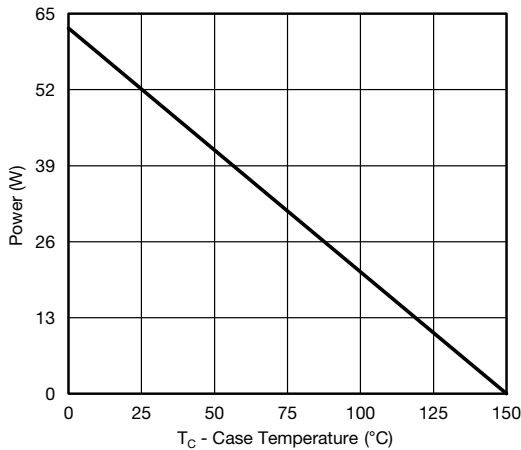
Safe Operating Area, Junction-to-Ambient



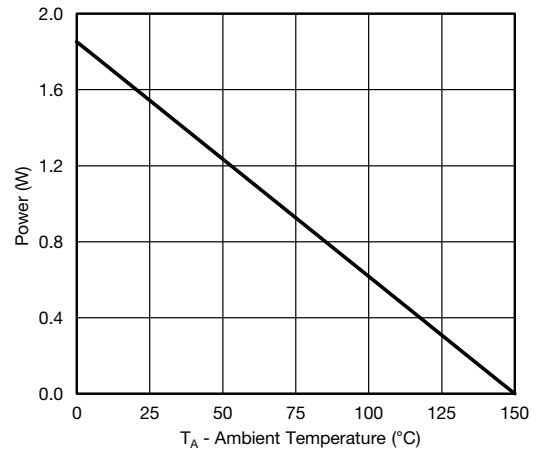
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



Power Derating, Junction-to-Case



Power Derating, Junction-to-Ambient

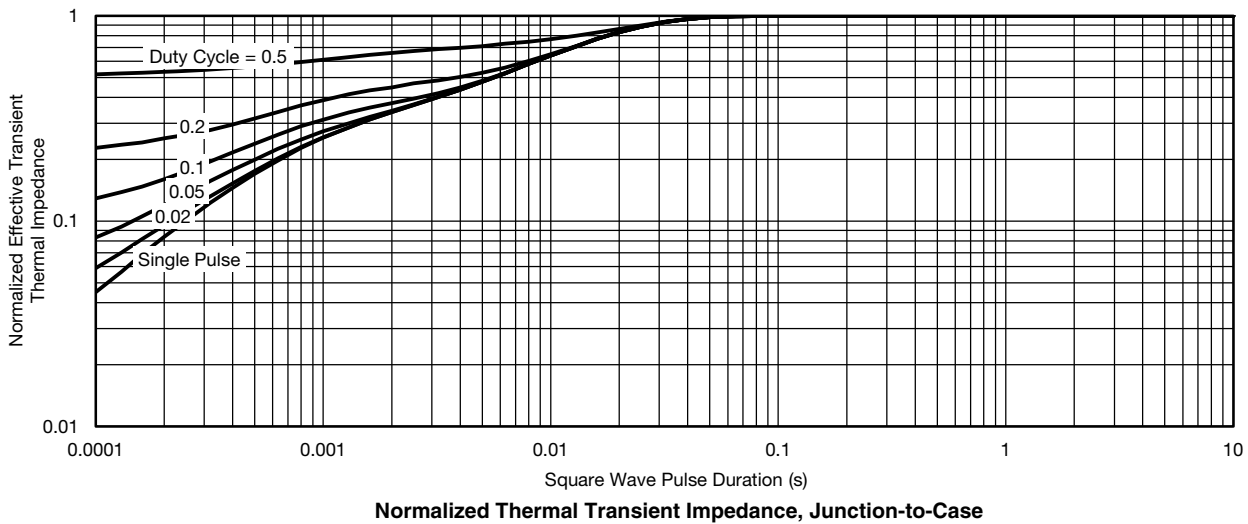
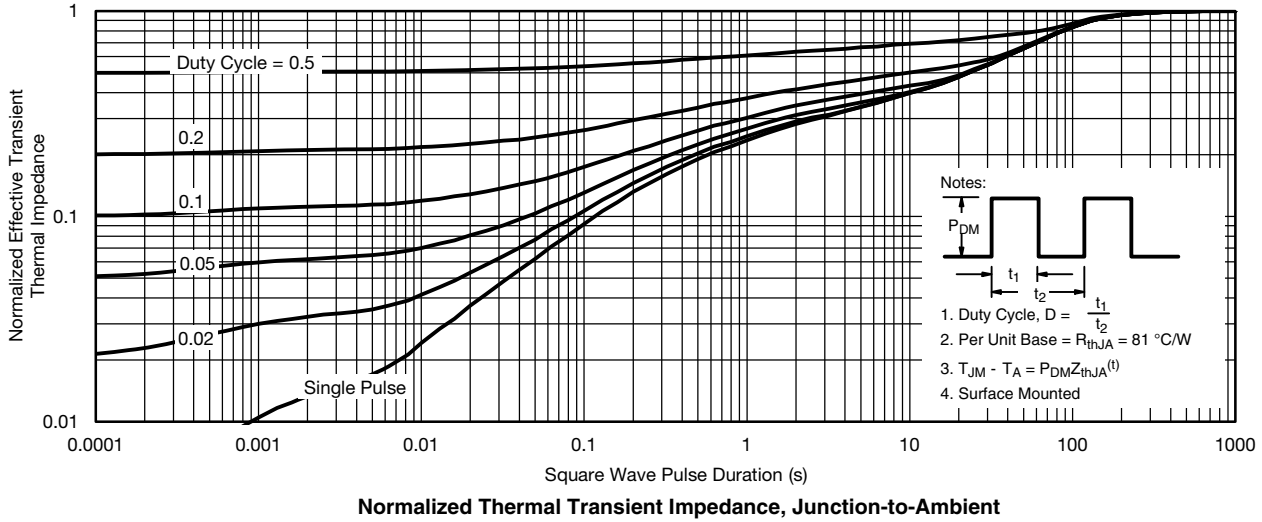
* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63684.

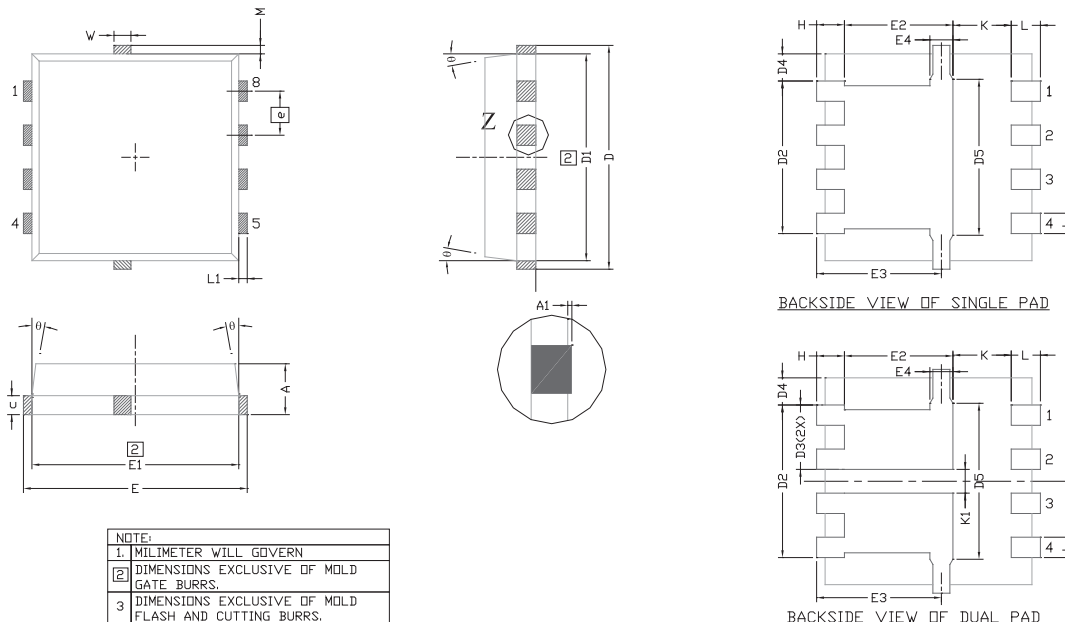


www.vishay.com

Package Information

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PowerPAK® 1212-8T



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.70	0.75	0.80	0.028	0.030	0.031
A1	0.00	-	0.05	0.000	-	0.002
b	0.23	0.30	0.41	0.009	0.012	0.016
c	0.23	0.28	0.33	0.009	0.011	0.013
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
D3	0.48	-	0.89	0.019	-	0.035
D4	0.47 TYP.			0.0185 TYP.		
D5	2.3 TYP.			0.090 TYP.		
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	1.75	1.85	1.98	0.069	0.073	0.078
E4	0.34 TYP.			0.013 TYP.		
e	0.65 BSC			0.026 BSC		
K	0.86 TYP.			0.034 TYP.		
K1	0.35	-	-	0.014	-	-
H	0.30	0.41	0.51	0.012	0.016	0.020
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
M	0.125 TYP.			0.005 TYP.		
ECN: T13-0056-Rev. A, 18-Feb-13						
DWG: 6012						



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